
HD74HCT620/HD74HCT623

Octal Bus Transceivers (with inverted 3-state outputs)/
Octal Bus Transceivers (with 3-state outputs)

HITACHI

Description

This octal transceiver is designed for asynchronous two-way communication between data buses. The control function implementation allows for maximum flexibility in timing.

This device allows data transmission from A bus to the B bus or from the B bus to the A bus depending upon the logic levels at the enable inputs ($\overline{G}BA$ and GAB).

The enable inputs can be used to disable the device so that the buses are affectively isolated.

The dual-enable configuration gives these devices the capability to store data by simultaneous enabling of $\overline{G}BA$ and GAB . Each output reinforces its input in this transceiver configuration. Thus, when both control inputs are enabled and all other data sources to the two sets of bus lines are at high impedance, both sets of bus lines (16 in all) will remain at their last states. The 8-bit codes appearing on the two sets of buses will be identical for the HD74HCT623 or complementary for the HD74HCT620.

Features

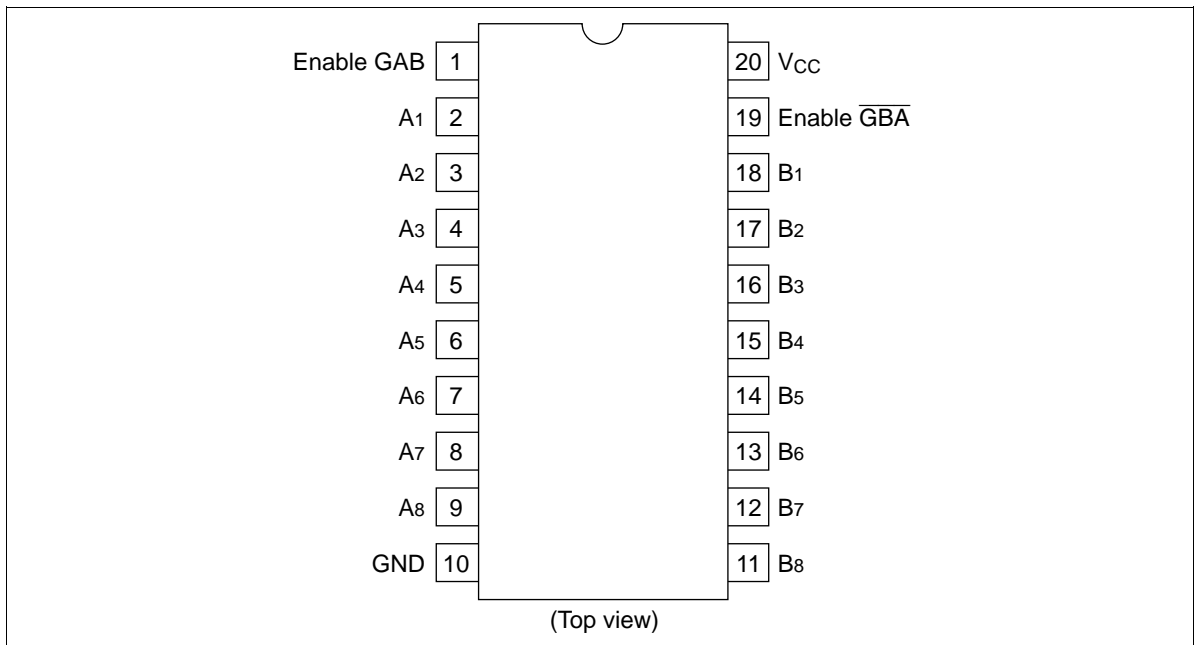
- LSTTL Output Logic Level Compatibility as well as CMOS Output Compatibility
- High Speed Operation: t_{pd} (Bus to Bus) = 15 ns typ ($C_L = 50$ pF)
- High Output Current: Fanout of 15 LSTTL Loads
- Wide Operating Voltage: $V_{CC} = 4.5$ to 5.5 V
- Low Input Current: 1 μ A max
- Low Quiescent Supply Current: I_{CC} (static) = 4 μ A max ($T_a = 25^\circ\text{C}$)

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Function Table

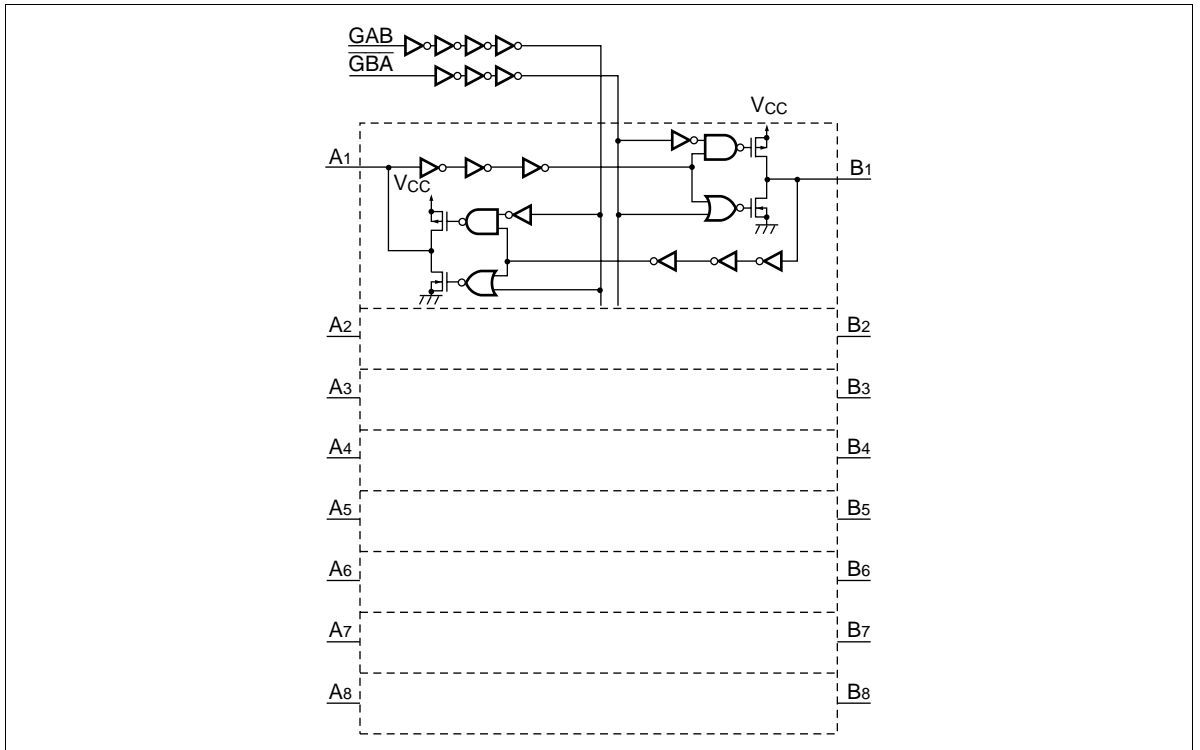
Enable Input		Operation	
$\overline{\text{GBA}}$	GAB	HD74HCT620	HD74HCT623
L	L	$\overline{\text{B}}$ data to A bus	B data to A bus
H	H	$\overline{\text{A}}$ data to B bus	A data to B bus
H	L	Isolation	Isolation
L	H	$\overline{\text{B}}$ data to A bus, $\overline{\text{A}}$ data to B bus	B data to A bus, A data to B bus

Pin Arrangement

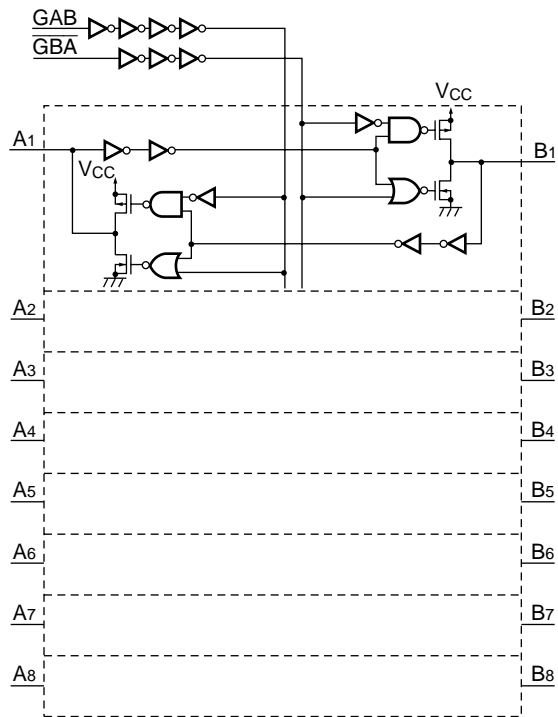


Block Diagram

HD74HCT620



HD74HCT623



Absolute Maximum Ratings

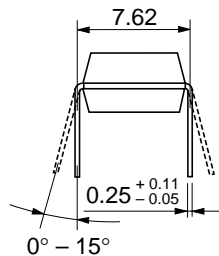
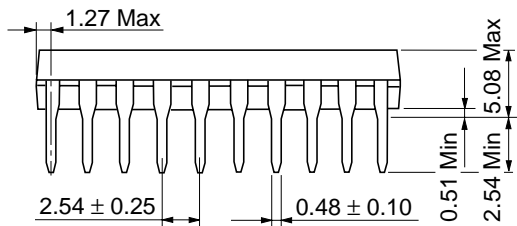
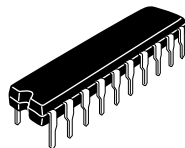
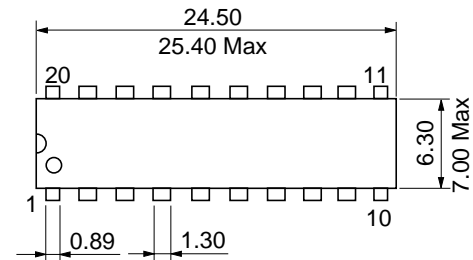
Item	Symbol	Rating	Unit
Supply voltage range	V_{CC}	-0.5 to +7.0	V
Input voltage	V_{IN}	-0.5 to $V_{CC} + 0.5$	V
Output voltage	V_{OUT}	-0.5 to $V_{CC} + 0.5$	V
DC current drain per pin	I_{OUT}	± 35	mA
DC current drain per V_{CC} , GND	I_{CC} , I_{GND}	± 75	mA
DC input diode current	I_{IK}	± 20	mA
DC output diode current	I_{OK}	± 20	mA
Power dissipation per package	P_T	500	mW
Storage temperature	T_{stg}	-65 to +150	$^{\circ}C$

DC Characteristics

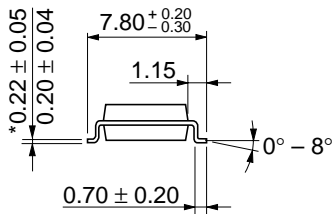
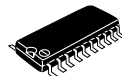
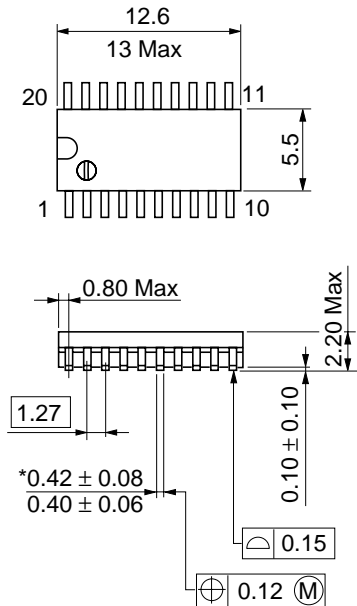
Item	Symbol	Ta = 25°C		Ta = -40 to +85°C		Unit	Test Conditions	
		Min	Typ	Max	Min		Max	V _{CC} (V)
Input voltage	V _{IH}	2.0	—	—	2.0	—	V	4.5 to 5.5
	V _{IL}	—	—	0.8	—	0.8	V	4.5 to 5.5
Output voltage	V _{OH}	4.4	—	—	4.4	—	V	4.5 Vin = V _{IH} or V _{IL} I _{OH} = -20 μA
		4.18	—	—	4.13	—		4.5 I _{OH} = -6 mA
	V _{OL}	—	—	0.1	—	0.1	V	4.5 Vin = V _{IH} or V _{IL} I _{OL} = 20 μA
		—	—	0.26	—	0.33		4.5 I _{OL} = 6 mA
Off-state output current	I _{OZ}	—	—	±0.5	—	±5.0	μA	5.5 Vin = V _{IH} or V _{IL} , Vout = V _{CC} or GND
Input current	I _{in}	—	—	±0.1	—	±1.0	μA	5.5 Vin = V _{CC} or GND
Quiescent supply current	I _{CC}	—	—	4.0	—	40	μA	5.5 Vin = V _{CC} or GND, Iout = 0 μA

AC Characteristics (C_L = 50 pF, Input t_r = t_f = 6 ns)

Item	Symbol	Ta = 25°C		Ta = -40 to +85°C		Unit	Test Conditions	
		Min	Typ	Max	Min		Max	V _{CC} (V)
Propagation delay time	t _{PLH}	—	13	20	—	25	ns	4.5
	t _{PHL}	—	16	20	—	25		4.5
Output enable time	t _{ZH}	—	16	30	—	38	ns	4.5
	t _{ZL}	—	16	30	—	38		4.5
Output disable time	t _{HZ}	—	19	30	—	38	ns	4.5
	t _{LZ}	—	21	30	—	38		4.5
Output rise/fall time	t _{TLH}	—	4	12	—	15	ns	4.5
	t _{THL}	—	—	—	—	—		—
Input capacitance	C _{in}	—	5	10	—	10	pF	—

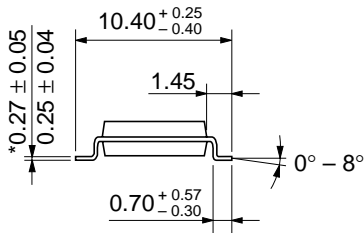
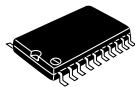
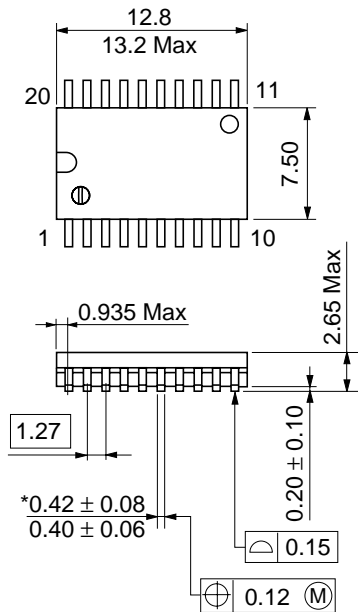


Hitachi Code	DP-20N
JEDEC	—
EIAJ	Conforms
Weight (reference value)	1.26 g



*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-20DA
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.31 g



Hitachi Code	FP-20DB
JEDEC	Conforms
EIAJ	—
Weight (reference value)	0.52 g

*Dimension including the plating thickness
 Base material dimension

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